V_{RRM}	650	V
I_F	6	A
Q_c	25	nC

Features

- Zero Forward Recovery Voltage
- Zero Reverse Recovery Current
- Excellent Surge Current Capability
- Temperature Independent Switching
- Positive Temperature Coefficient on V_F
- High Frequency Operation

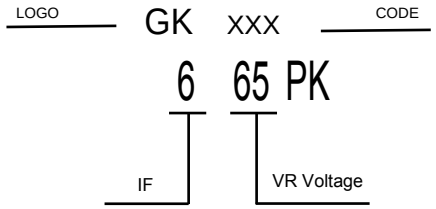
Benefits

- Increased Power Density
- Essentially no Switching Losses
- Reduction of Heat Sink Requirements
- Higher Efficiency
- Reduced EMI

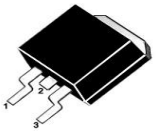
Applications

- Uninterruptible Power Supplies
- Switch Mode Power Supplies
- Power Factor Correction
- Motor Drivers

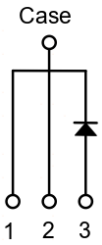




TO-263



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings (T_j=25℃ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit
V_{RRM}	Repetitive peak reverse voltage		650	V
I_F	Continuous forward current	T_c=25°C T_c=160°C	37 6	A
I_{FSM}	Non-Repetitive forward surge current	T_c=25°C, t_p=10ms, Half Sine Wave	60	A
$\int i^2dt$	i^2t value	T_c=25°C, t_p=10ms	18	A^2s
P_{tot}	Power dissipation	T_c=25°C T_c=110°C	136 59	W
T_j	Operating junction temperature		-55~175	°C
T_{stg}	Storage temperature		-55~175	°C

ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
V_{DC}	DC blocking voltage	T_j=25°C	650			V
V_F	Diode forward voltage	I_F=6A T_j=25°C I_F=6A T_j=135°C I_F=6A T_j=175°C		1.25 1.32 1.38	1.48 1.74 1.90	V
I_R	Reverse current	V_R=650V T_j=25°C V_R=650V T_j=175°C		0.5 15	50 200	μA

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
Q_C	Total capactive charge	V_R=400V T_j=25°C $Q_C = \int_0^{V_R} C(V)dV$		25		nC
C	Total capacitance	V_R=1V f=1MHz V_R=300V f=1MHz V_R=600V f=1MHz		350 42 36		pF
E_C	Capacitance stored energy	V_R=400V		3.8		μJ

Thermal Characteristics

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		1.05		°C/W

RATING AND CHARACTERISTIC CURVES

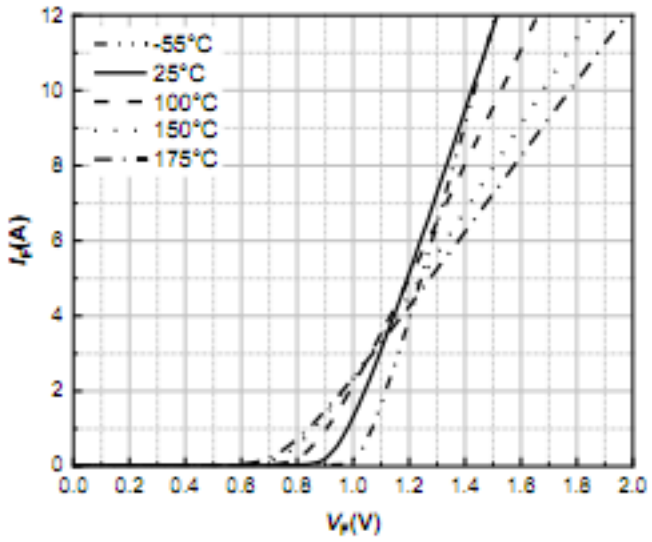


Figure 1. Typical forward characteristics

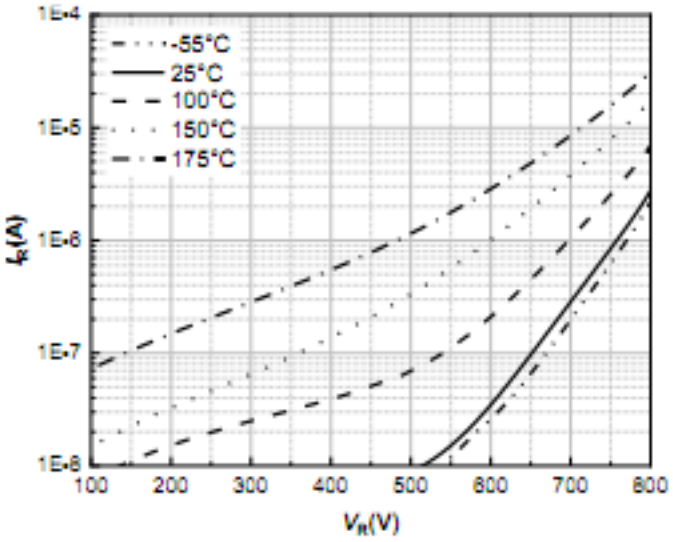


Figure 2. Typical reverse current as function of reverse voltage

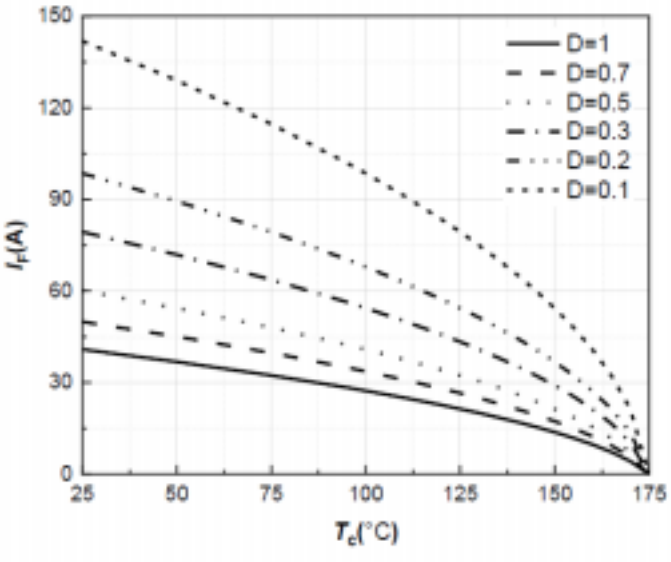


Figure 3. Diode forward current as function of temperature, D=duty cycle

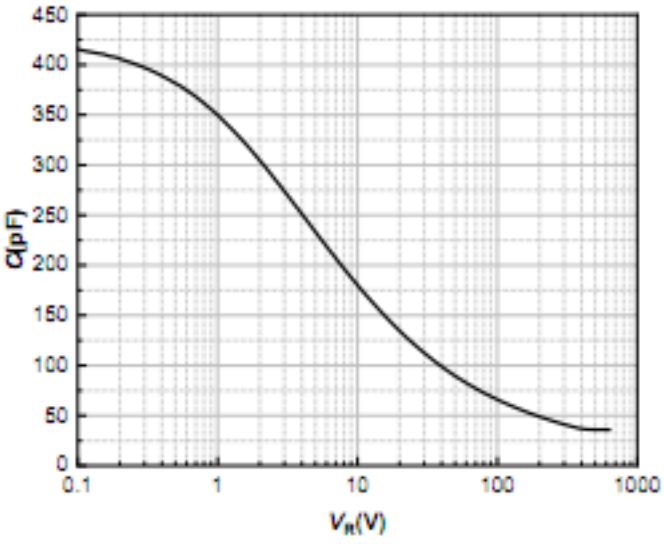


Figure 4. Typical capacitance as function of reverse voltage, C=f(V_R); T_j=25°C; f=1 MHz

RATING AND CHARACTERISTIC CURVES

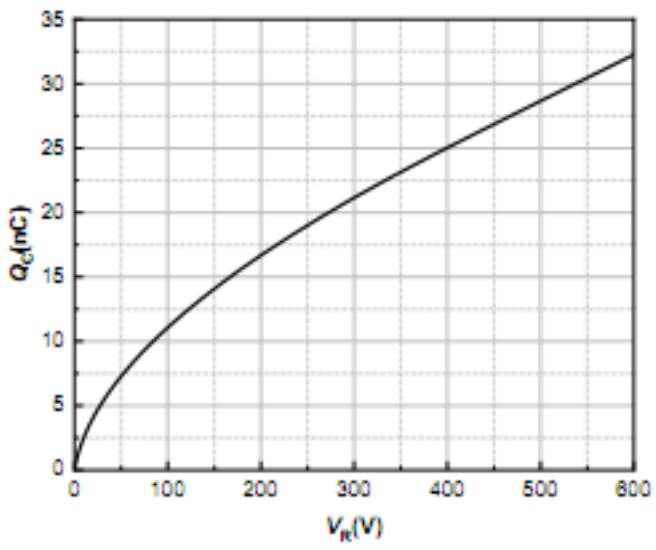


Figure 5. Typical reverse charge as function of reverse voltage

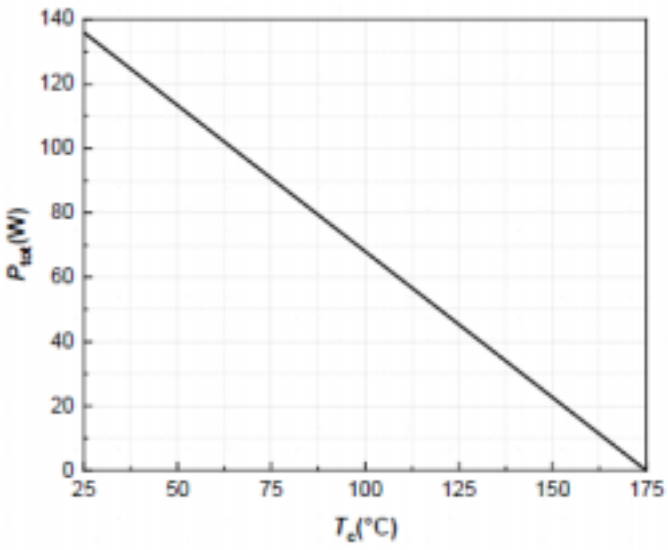


Figure 6. Power dissipation as function of case temperature

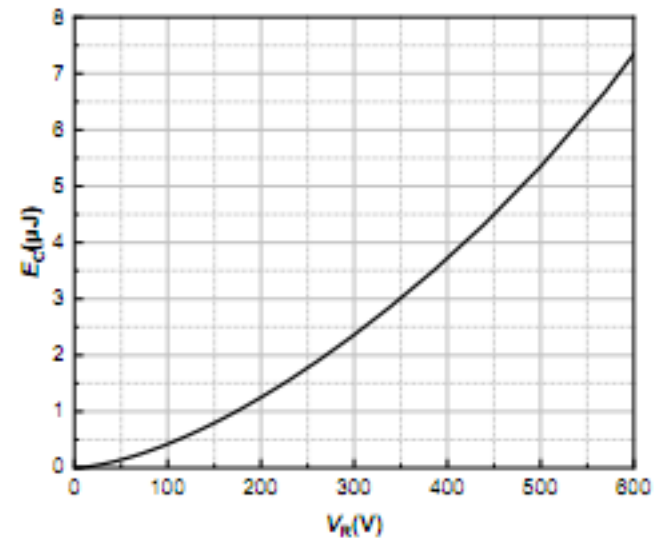


Figure 7.Capacitance stored energy

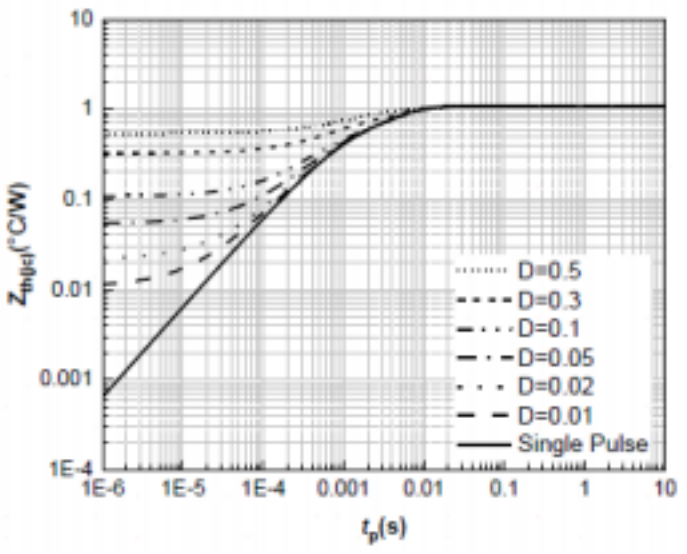
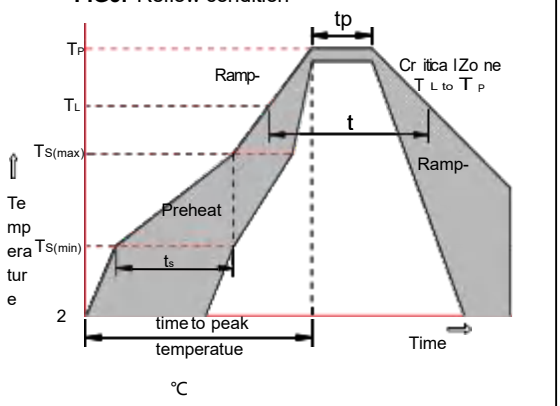


Figure 8. Max. transient thermal impedance, $Z_{th(j-c)} = f(t_p)$, parameter: $D = t_p / T$

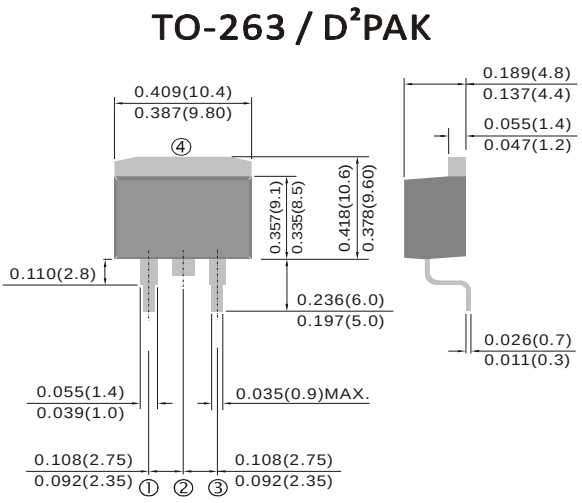
Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

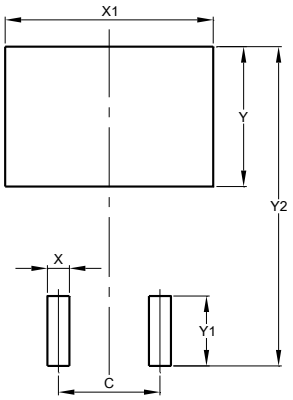
FIG5: Reflow condition



Package Dimensions & Suggested Pad Layout



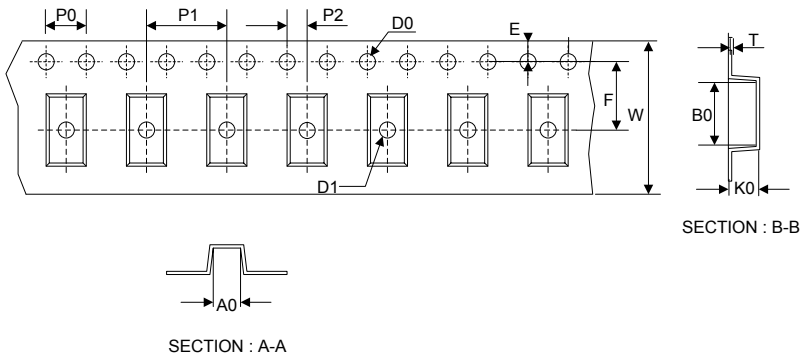
Dimensions in inches and (millimeters)



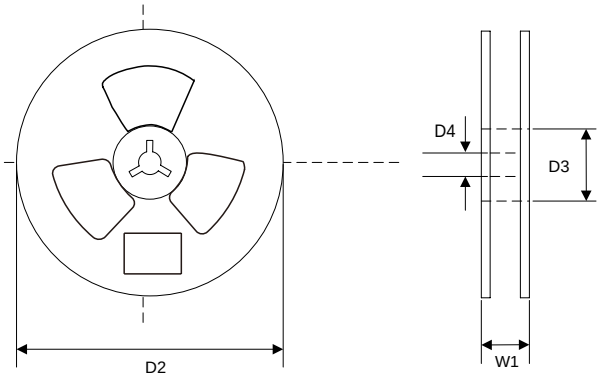
Dimensions	Value (in mm)
C	5.05
X	1.40
X1	11.00
Y	9.20
Y1	4.00
Y2	16.60

Tape & rell specification

Tape



13” Reel



Symbol	Dimension (mm)
P0	4.00±0.20
P1	16.00±0.20
P2	2.00±0.20
D0	1.50±0.20
D1	1.50±0.20
E	1.75±0.15
F	11.50±0.20
W	24.00±0.40
A0	10.50±0.20
B0	16.00±0.25
K0	5.20±0.25
T	0.35±0.10
D2	330.0±5.0
D3	73Min.
D4	14.0±2.5
W1	28.00±2.0
Quantity: 800PCS	